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solution which contains hydrogen peroxide, hydrazine fluoride salt, and water, concentration of said hydrazine fluoride salt in said processing solution being in a range of about 0.1 to 3 mol/l;

(c) removing said insulating film after said step (b) thereby to expose the surface of said silicon wafer; and

(d) subjecting said silicon wafer to a heat-treatment after said step (c) thereby to form a gate oxide film over said silicon wafer.

Please add the following new claims to the application:

--34. A method of manufacturing a semiconductor integrated circuit device according to claim 23, wherein said processing solution has a pH in a range of 6 to 11.

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35. A method of manufacturing a semiconductor integrated circuit device according to claim 34, wherein said processing solution etches the silicon oxide but does not etch the silicon wafer.

36. A method of manufacturing a semiconductor integrated circuit device according to claim 23, wherein said processing solution etches the silicon oxide but does not etch the silicon wafer.

37. A method of manufacturing a semiconductor integrated circuit device according to claim 20, wherein said processing solution etches the silicon oxide but does not etch the silicon wafer.--
